



TRW54601

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

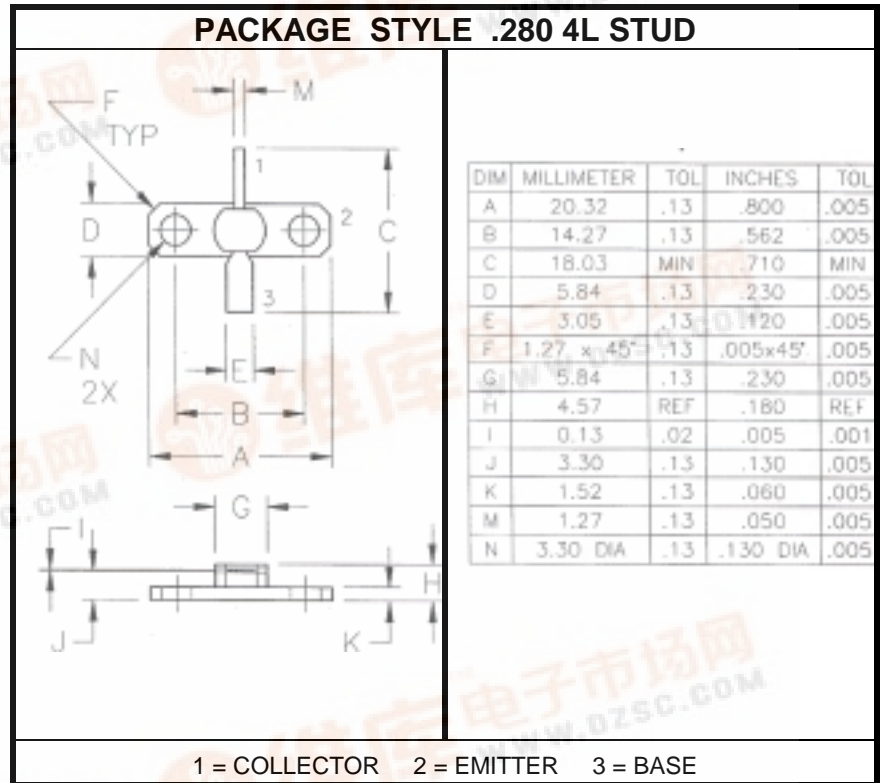
The **ASI TRW54601** is Designed for General Purpose Oscillator Applications up to 2.3 GHz.

FEATURES:

- Diffused Ballast Resistors
- **Omnigold™** Metalization System
- Common Emitter

MAXIMUM RATINGS

I_C	400 mA
V_{CES}	50 V
P_{DISS}	3.0 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	35 °C/W



CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$	22			V
BV_{CES}	$I_C = 10\text{ mA}$	50			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 28\text{ V}$			0.5	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	20			---
C_{OB}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		2.4	3.0	pF
P_G	$V_{CE} = 20\text{ V}$ $I_C = 120\text{ mA}$ $f = 2.3\text{ GHz}$	8.5	9.5		dB
$VSRW$	$P_{OUT} = 0.5\text{ W}$			30:0	---

